

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS C6

650V CoolMOS™ C6 Power Transistor  
IPx65R380C6

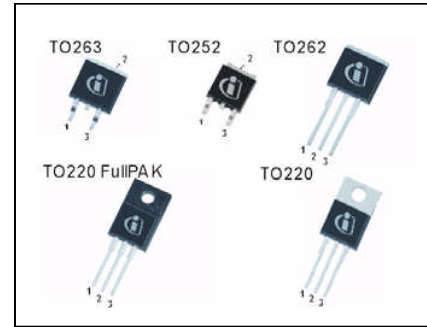
## Data Sheet

Rev. 2.0, 2010-10-22  
Final

**Industrial & Multimarket**



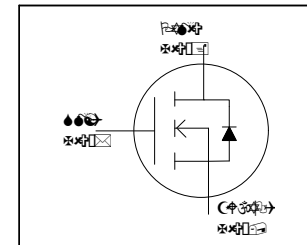
CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.



- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC<sup>1)</sup> qualified, Pb-free plating, Halogen free<sup>2)</sup>

h

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.



Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



Q t

$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	0.38	$\Omega$
$Q_{g,typ}$	39	nC
$I_{D,pulse}$	29	A
$E_{oss} @ 400V$	2.8	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

O	I	y	u
IPD65R380C6	PG-TO252	65C6380	<a href="#">IFX CoolMOS Webpage</a> <a href="#">IFX Design tools</a>
IPI65R380C6	PG-TO262		
IPB65R380C6	PG-TO263		
IPP65R380C6	PG-TO220		
IPA65R380C6	PG-TO220 FullPAK		

1) J-STD20 and JESD22  
 2) no PG-To252

	I		
Q	m	.....	2
		I	3
R	y	.....	4
S		.....	5
T	n	.....	6
V	n	.....	8
a		.....	13
b		.....	14
c	r	.....	19

R y

 at  $T_j = 25\text{ °C}$ , unless otherwise specified.

R y

						O I
		y M	M	y M		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	10.6	A	$T_C = 25\text{ °C}$
				6.7		$T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	29	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	215	mJ	$I_D = 1.8\text{ A}, V_{DD} = 50\text{ V}$ (see table 21)
Avalanche energy, repetitive	$E_{AR}$	-	-	0.32		$I_D = 1.8\text{ A}, V_{DD} = 50\text{ V}$
Avalanche current, repetitive	$I_{AR}$	-	-	1.8	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 480\text{ V}$
Gate source voltage	$V_{GS}$	-20	-	20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation for TO-220, TO-252, TO-262, TO-263	$P_{tot}$	-	-	83	W	$T_C = 25\text{ °C}$
Power dissipation for TO-220 FullPAK	$P_{tot}$	-	-	31	W	$T_C = 25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	
Mounting torque TO-220		-	-	60	Ncm	M3 and M3.5 screws
Mounting torque TO-220 FullPAK				50		M2.5 screws
Continuous diode forward current	$I_S$	-	-	9.2	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	29	A	$T_C = 25\text{ °C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 480\text{ V}, I_{SD} \leq I_D,$ $T_j = 125\text{ °C}$
Maximum diode commutation speed <sup>3)</sup>	$di_f/dt$			500	A/ $\mu\text{s}$	

 1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$ 

 2) Pulse width  $t_p$  limited by  $T_{j,max}$ 

 3) Identical low side and high side switch with identical  $R_G$

S

S		IRRP. IRaR				O I
		y M	M	y M		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.5	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

T		IRRPo ht				O I
		y M	M	y M		
Thermal resistance, junction - case	$R_{thJC}$	-	-	4.0	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	80		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

V		IRaS. IRVR				O I
		y M	M	y M		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.5	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		SMD version, device on PCB, minimal footprint
			35			SMD version, device on PCB, 6cm <sup>2</sup> cooling area <sup>1)</sup>
Soldering temperature, wave- & reflowsoldering allowed	$T_{sold}$	-	-	260	°C	reflow MSL1

1) Device on 40mm\*40mm\*1.5 epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70µm thick) copper area for drain connection. PCB is vertical without air stream cooling.

## T n

 Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified

a

						O / I
		y M	M	y M		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0\text{ V}, I_D=1.0\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		$V_{DS}=V_{GS}, I_D=0.32\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$
		-	10	-		$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.34	0.38	$\Omega$	$V_{GS}=10\text{ V}, I_D=3.2\text{ A}, T_j=25\text{ }^\circ\text{C}$
		-	0.89	-		$V_{GS}=10\text{ V}, I_D=3.2\text{ A}, T_j=150\text{ }^\circ\text{C}$
Gate resistance	$R_G$	-	17	-	$\Omega$	$f=1\text{ MHz}$ , open drain

b m

						O / I
		y M	M	y M		
Input capacitance	$C_{iss}$	-	710	-	pF	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V}, f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	41	-		
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	32	-		
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	140	-		
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=400\text{ V}, V_{GS}=13\text{ V}, I_D=4.9\text{ A}, R_G=3.4\text{ }\Omega$ (see table 20)
Rise time	$t_r$	-	12	-		
Turn-off delay time	$t_{d(off)}$	-	110	-		
Fall time	$t_f$	-	11	-		

 1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$ 

 2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

c p

						O I
		y M	M	y M		
IGate to source charge	$Q_{gs}$	-	4	-	nC	$V_{DD}=480\text{ V}$ , $I_D=4.9\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	20	-		
Gate charge total	$Q_g$	-	39	-		
Gate plateau voltage	$V_{plateau}$	-	5.5	-	V	

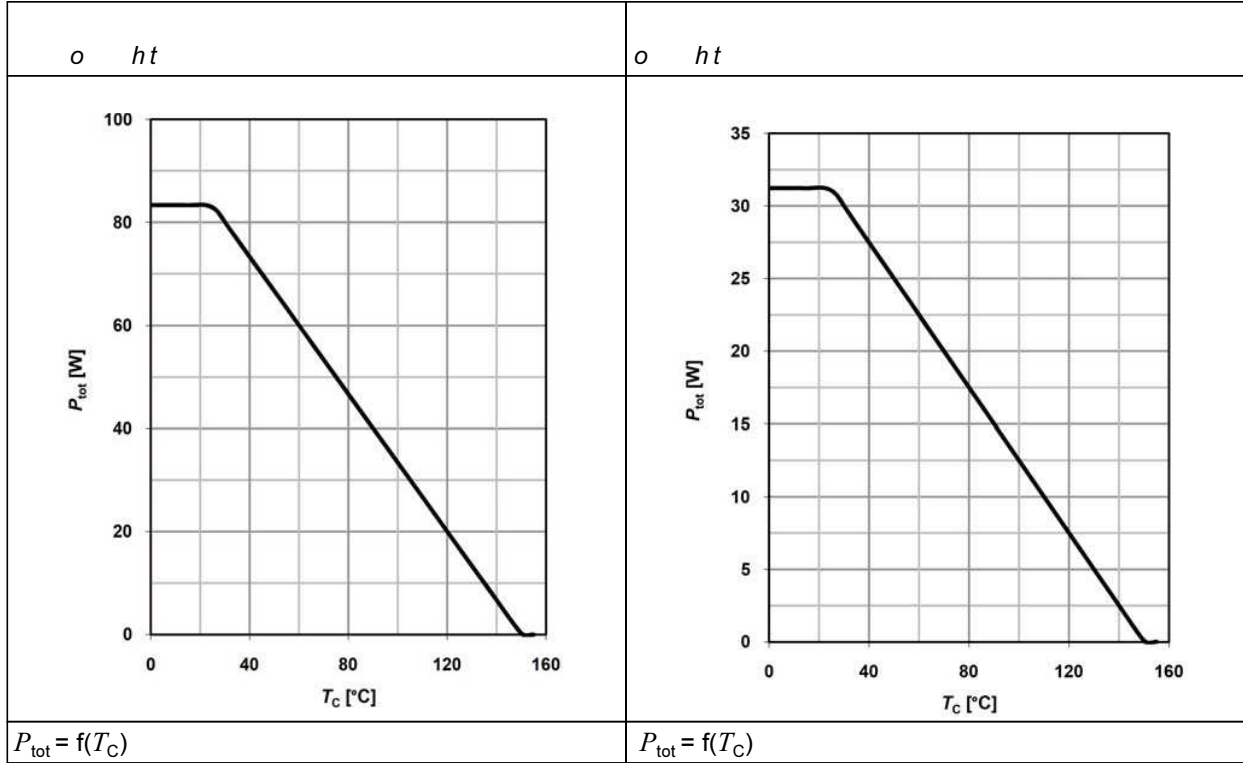
d

						O I
		y M	M	y M		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0\text{ V}$ , $I_F=4.9\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	280	-	ns	$V_R=400\text{ V}$ , $I_F=4.9\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22)
Reverse recovery charge	$Q_{rr}$	-	2.8	-	$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$	-	17	-	A	

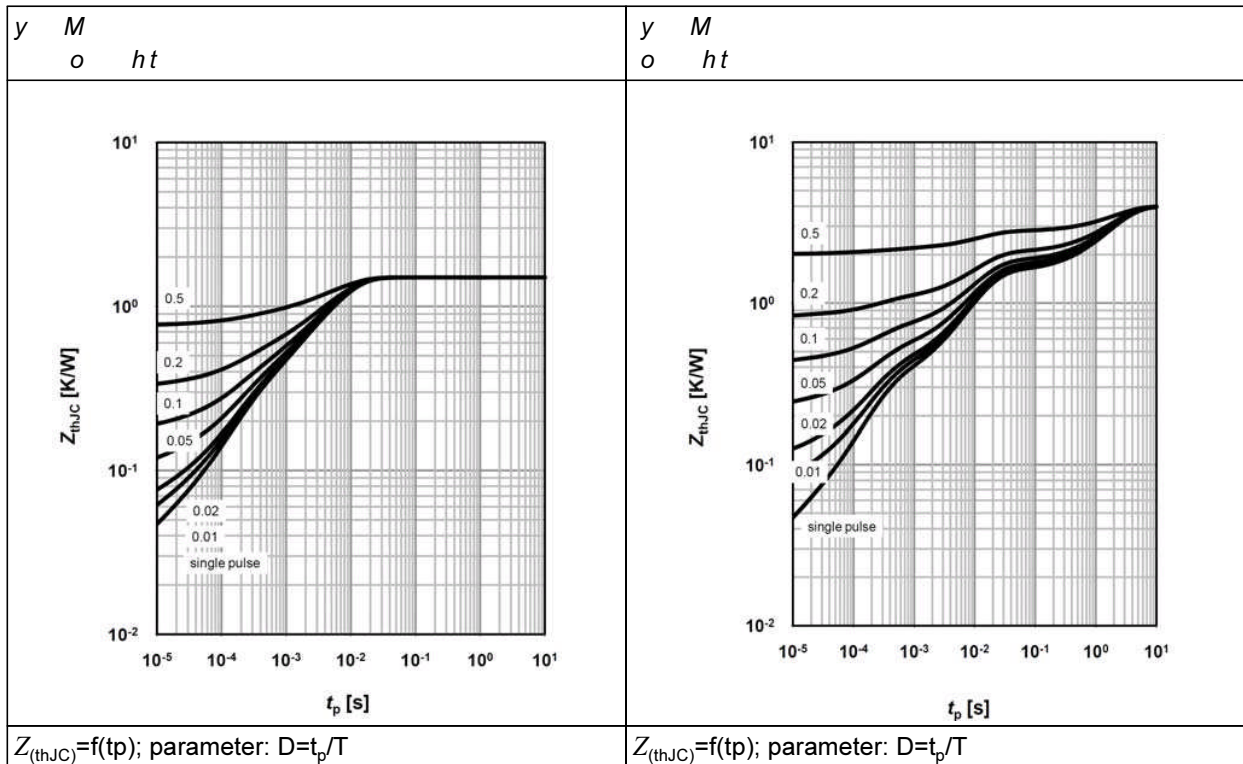
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n

QP

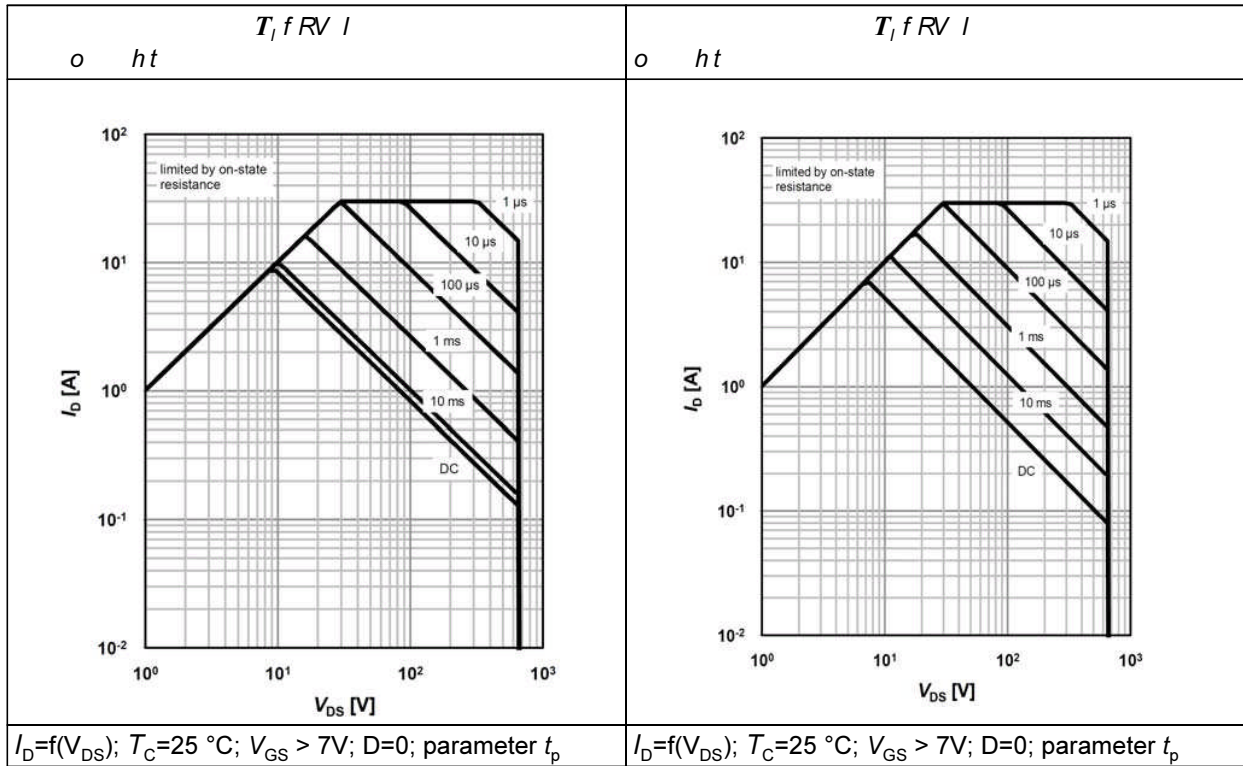


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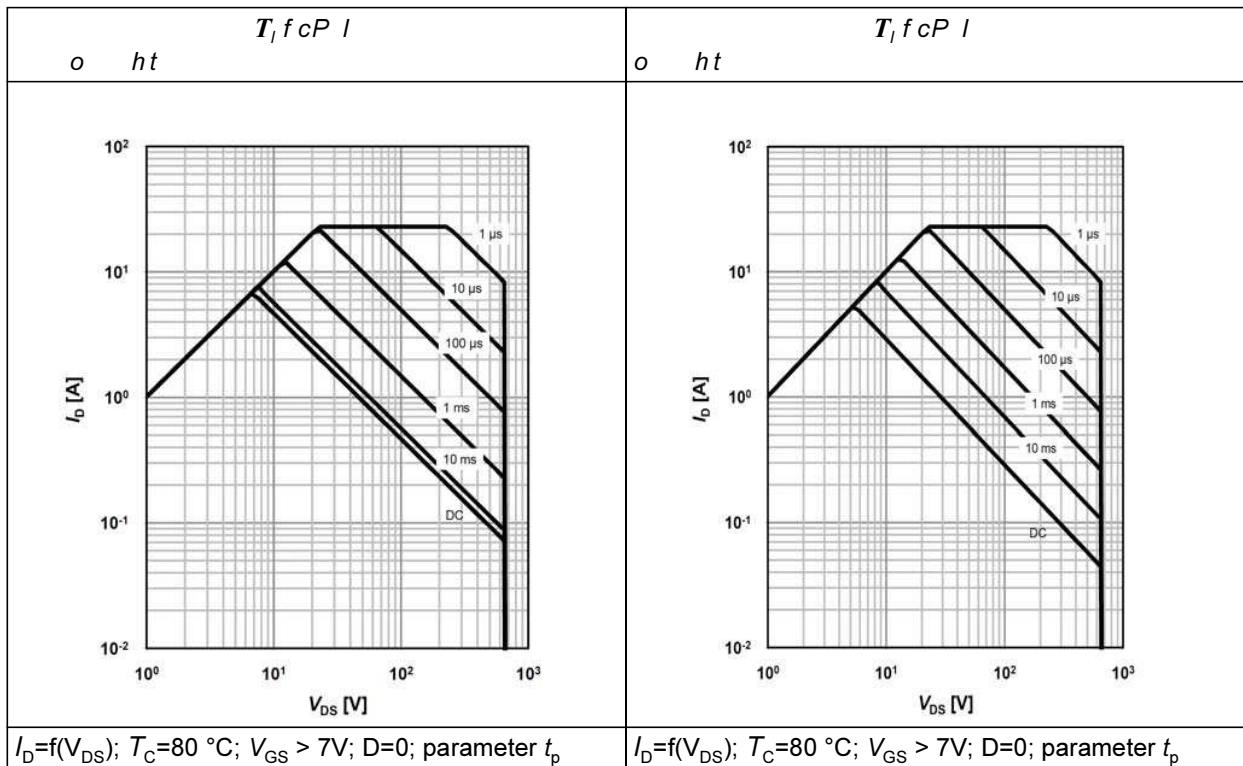




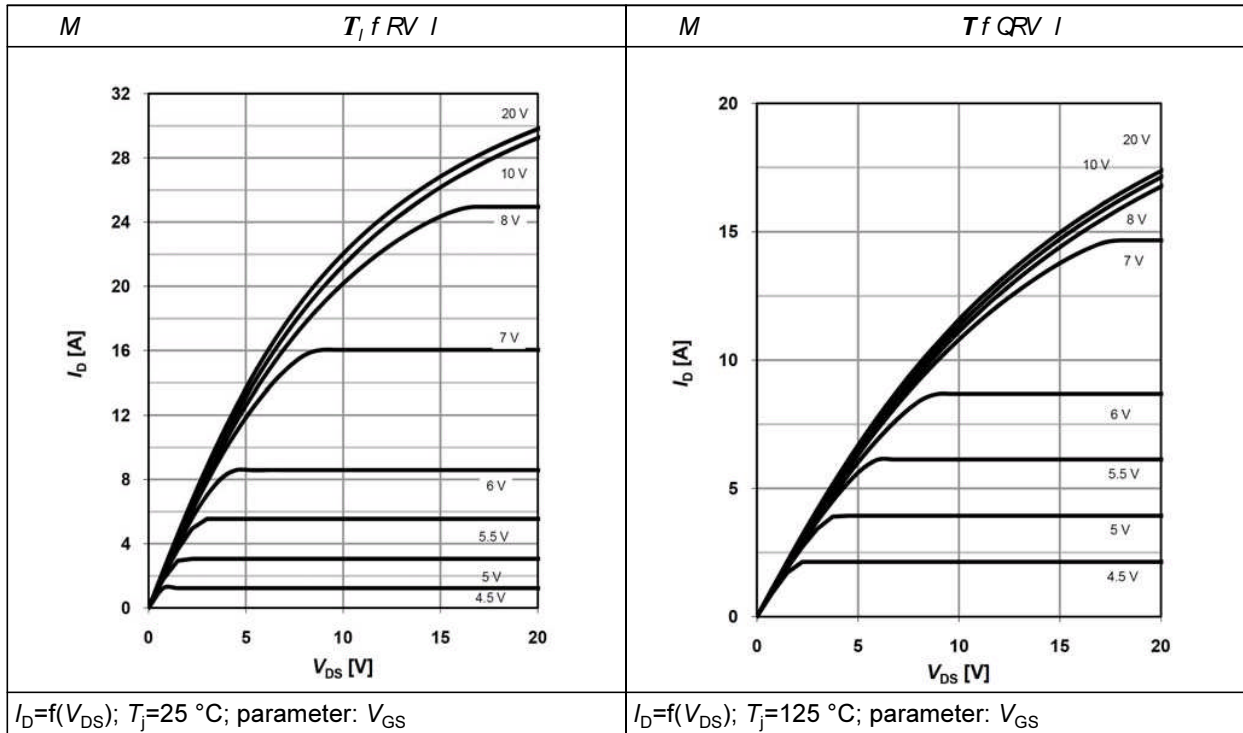
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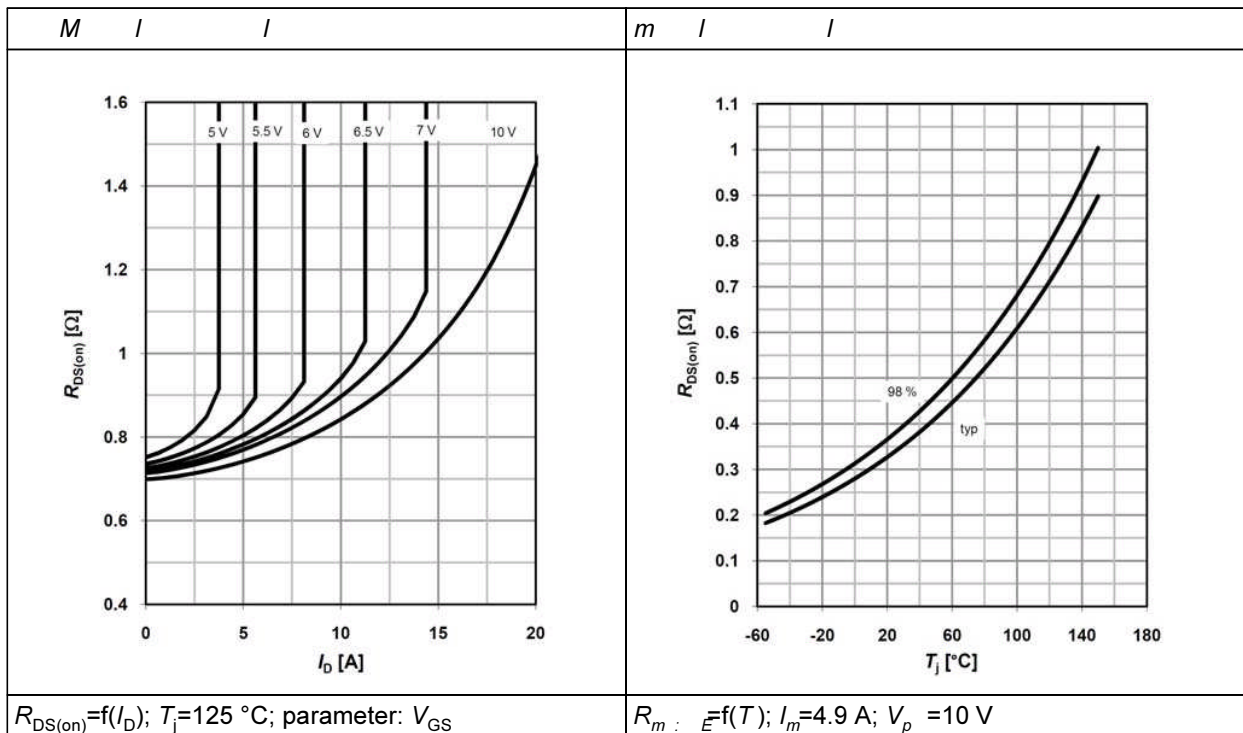
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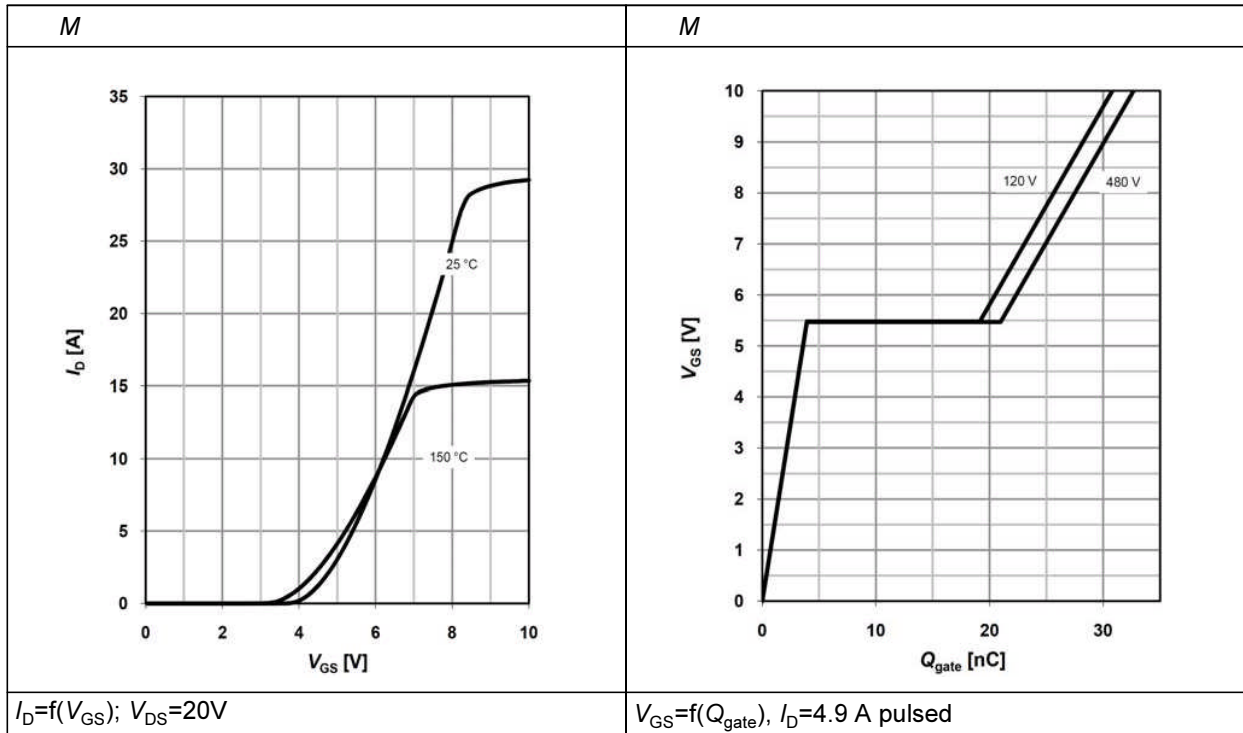
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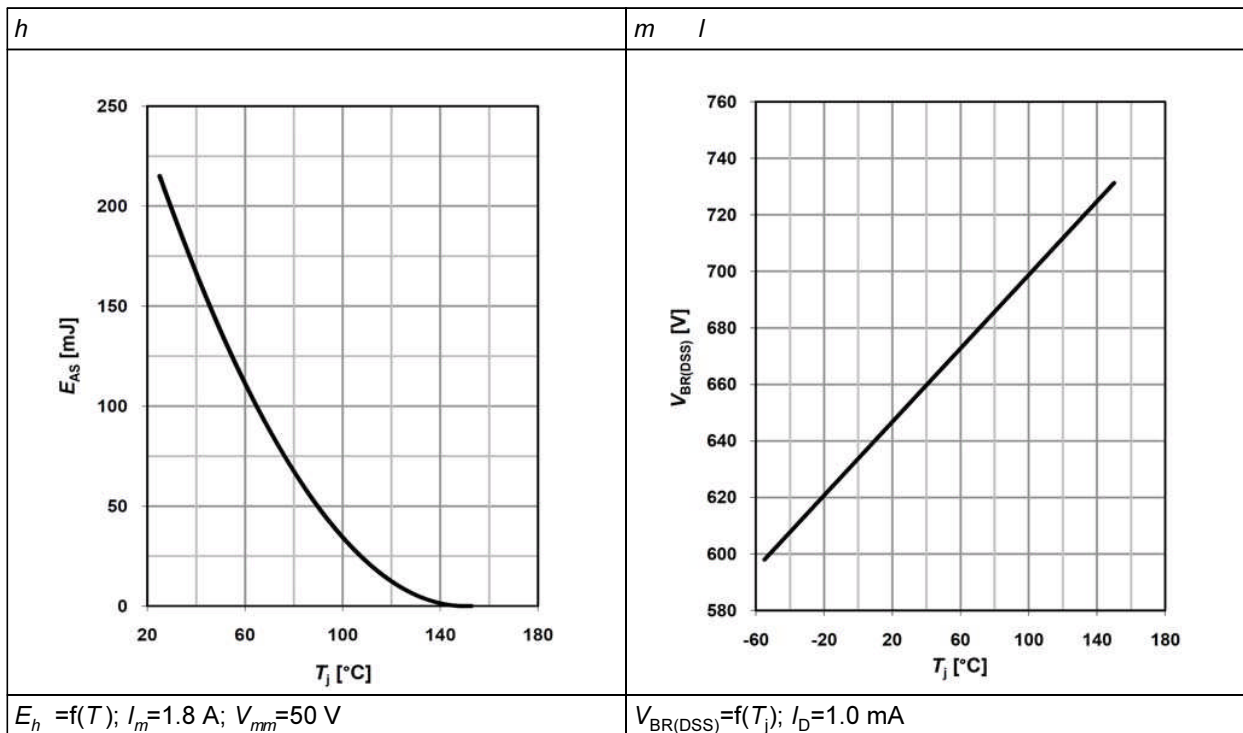
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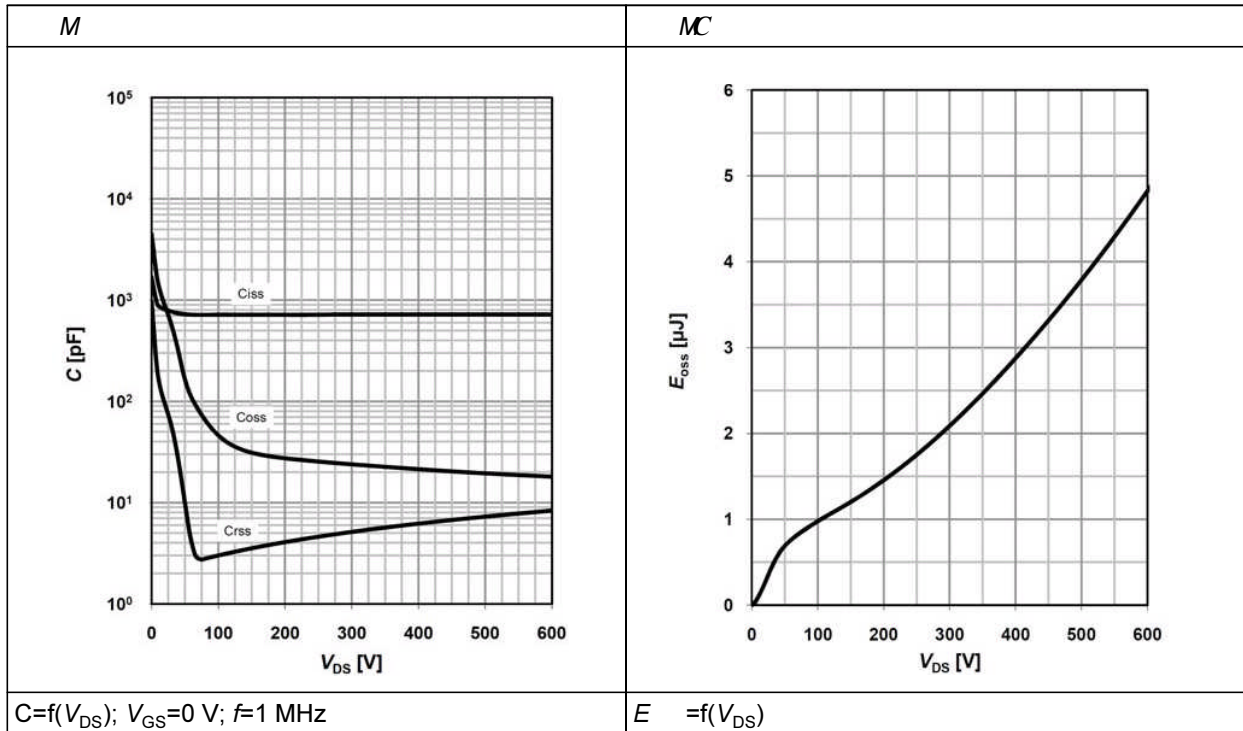
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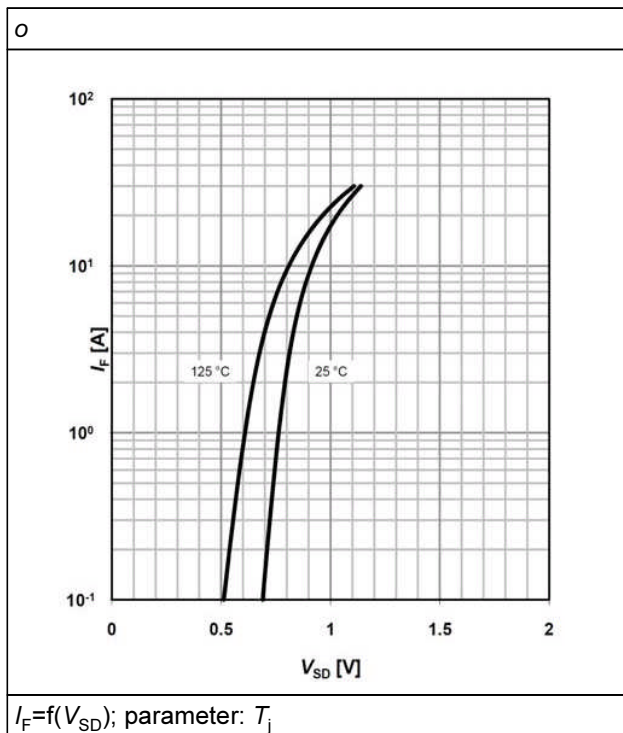
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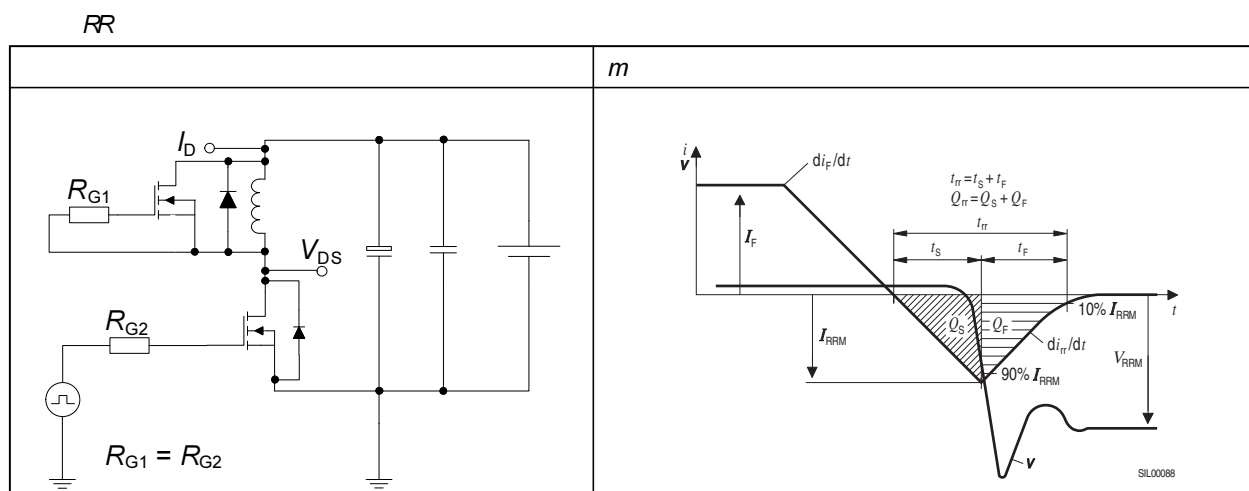
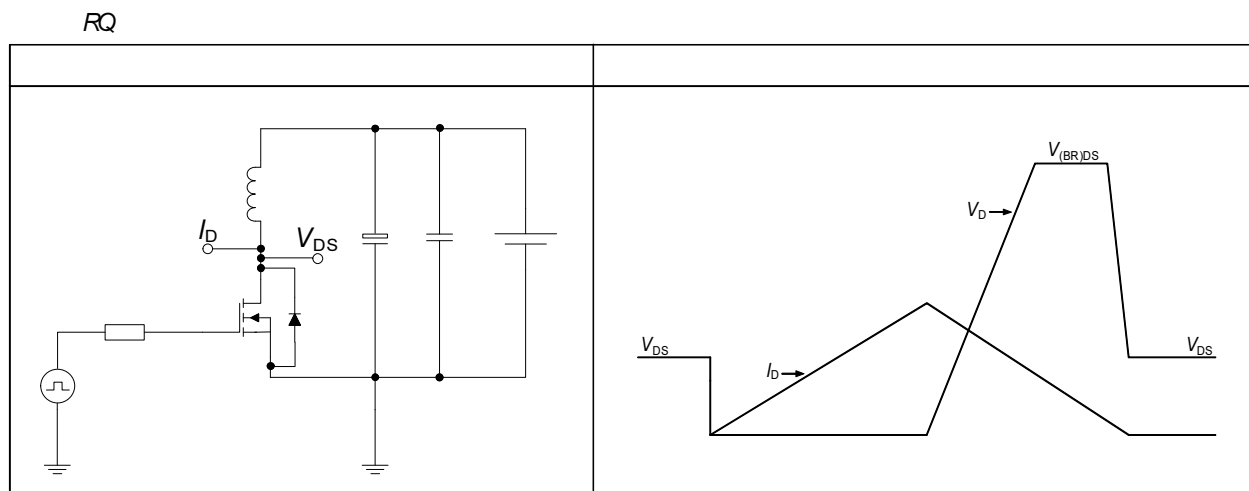
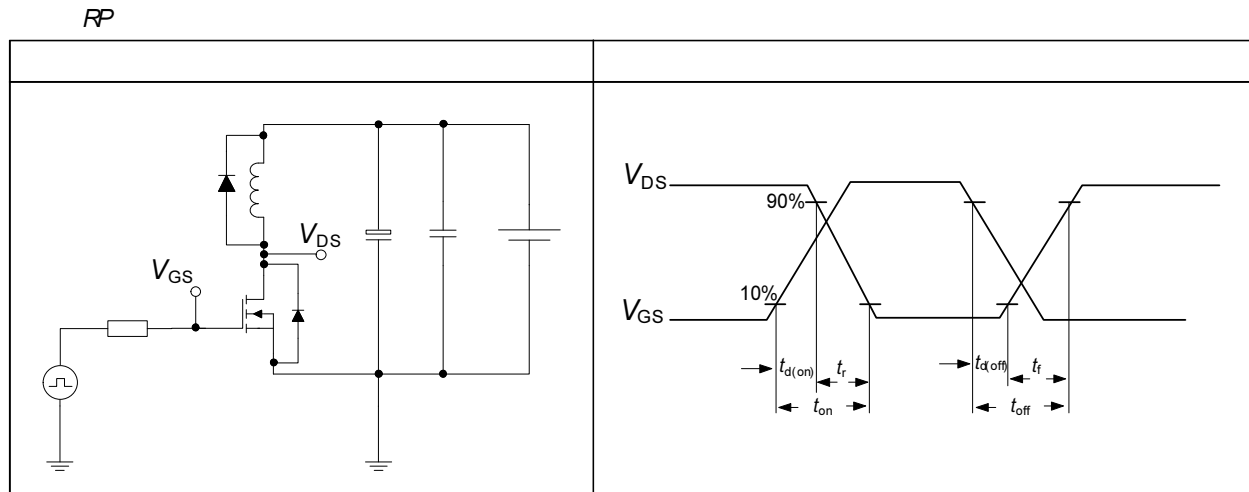
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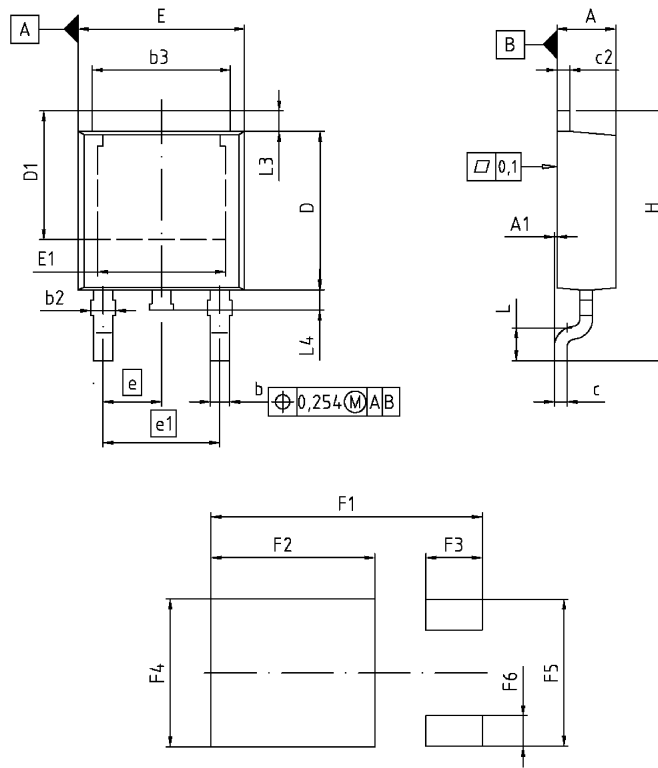
Qd



a



b



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

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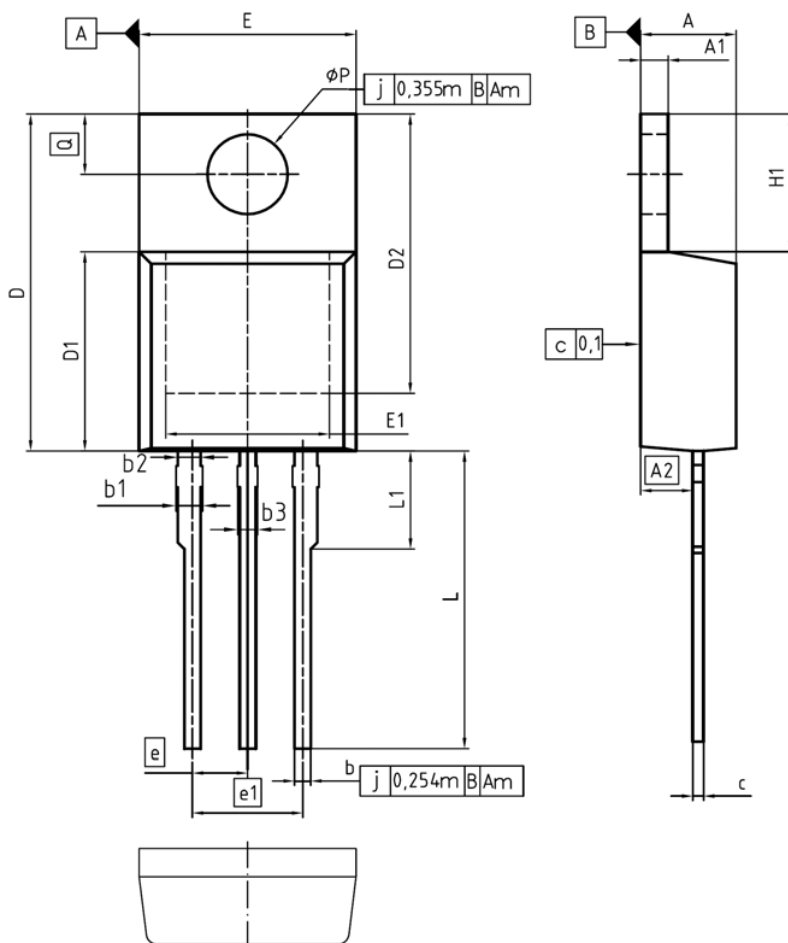
**ISSUE DATE**  
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**REVISION**  
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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
$\phi P$	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

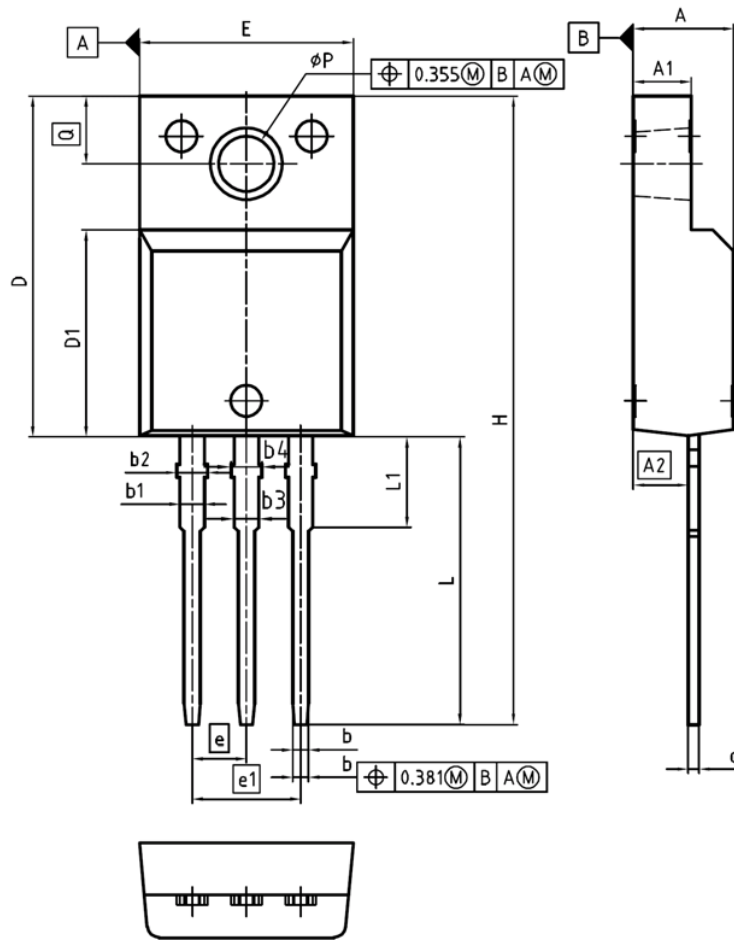
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ISSUE DATE  
23-08-2007

REVISION  
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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

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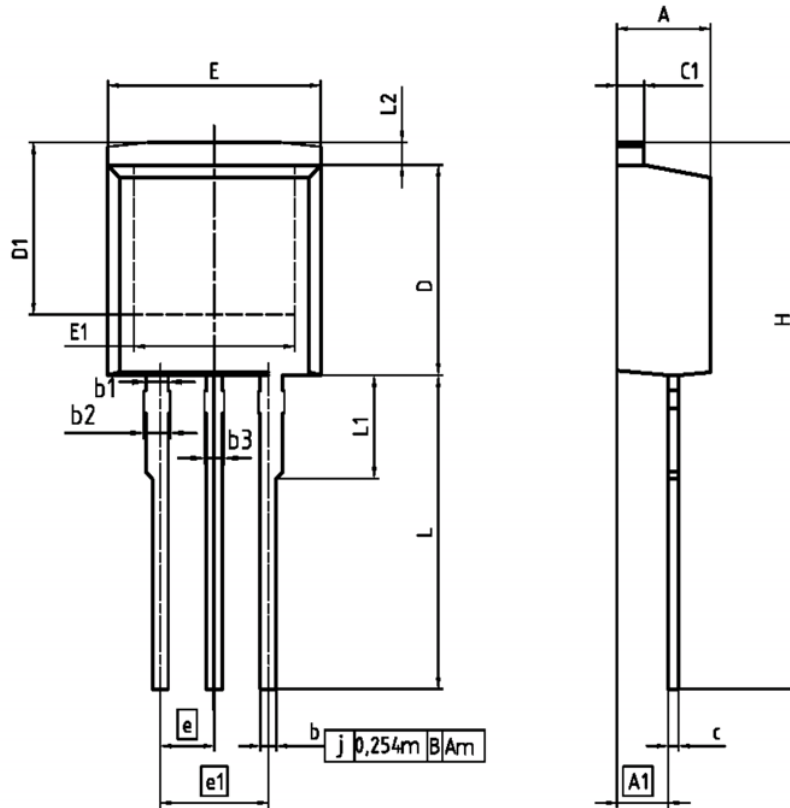
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ISSUE DATE  
08-03-2007

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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	2.150	2.718	0.085	0.107
b	0.650	0.864	0.026	0.034
b1	0.950	1.093	0.037	0.043
b2	0.950	1.400	0.037	0.055
b3	0.650	1.118	0.026	0.044
c	0.330	0.600	0.013	0.024
c1	1.170	1.400	0.046	0.055
D	8.509	8.450	0.335	0.372
D1	6.900	-	0.272	-
E	9.700	10.363	0.382	0.408
E1	6.500	8.600	0.256	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	-	4.800	-	0.189
L2	-	1.727	-	0.068

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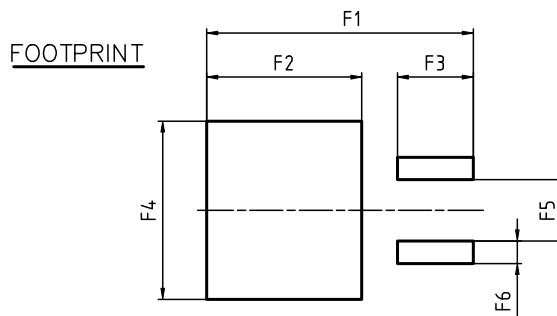
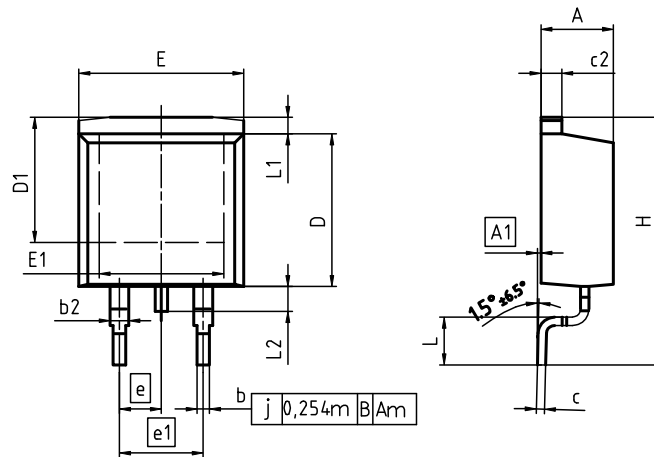
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DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.65	0.85	0.026	0.033
b2	0.95	1.15	0.037	0.045
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	7.10	7.90	0.280	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	2		2	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	3.65	3.85	0.144	0.152
F6	1.25	1.45	0.049	0.057

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ISSUE DATE  
**30-08-2007**

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Customer

	Release of final data sheet
2.0	Release of final data sheet

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Edition 2010-10-22  
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 Infineon Technologies AG  
 81726 Munich, Germany  
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